ABSTRACT

TITLE OF INVENTION: SCHOTTKY CONTACT STRUCTURE FOR SEMICONDUCTOR DEVICES AND METHOD FOR FORMING SUCH SCHOTTKY CONTACT STRUCTURE

A Schottky contact structure for a semiconductor device having a Schottky contact and an electrode for the contact structure disposed on the contact. The Schottky contact comprises: a first layer of a first metal in Schottky contact with a semiconductor; a second layer of a second metal on the first layer; a third layer of the first metal on the second layer; and a fourth layer of the second metal on the third layer. The electrode for the Schottky contact structure disposed on the Schottky contact comprises a third metal, the second metal providing a barrier against migration between the third metal and the first metal.

[Figure 4B]